



SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

EMH2412 — N-Channel Silicon MOSFET General-Purpose Switching Device Applications

Features

- Low ON-resistance
- Best suited for LiB charging and discharging switch
- Common-drain type
- 2.5V drive
- Halogen free compliance
- Protection diode in

Specifications

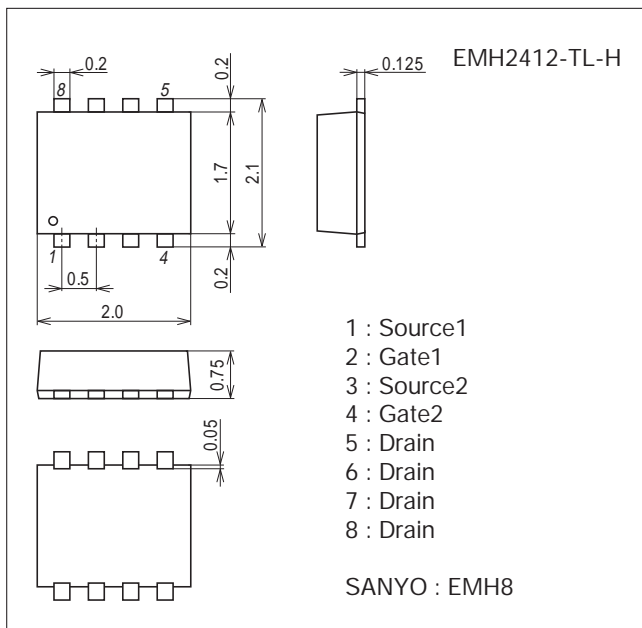
Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		24	V
Gate-to-Source Voltage	V _{GSS}		±12	V
Drain Current (DC)	I _D		6	A
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	60	A
Allowable Power Dissipation	P _D	When mounted on ceramic substrate (900mm ² ×0.8mm) 1unit	1.3	W
Total Dissipation	P _T	When mounted on ceramic substrate (900mm ² ×0.8mm)	1.4	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

Package Dimensions

unit : mm (typ)

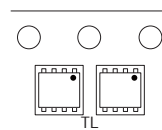
7045-006



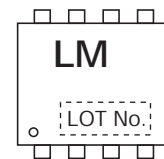
Product & Package Information

- Package : EMH8
- JEITA, JEDEC : -
- Minimum Packing Quantity : 3,000 pcs./reel

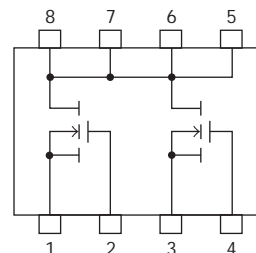
Taping Type : TL



Marking



Electrical Connection

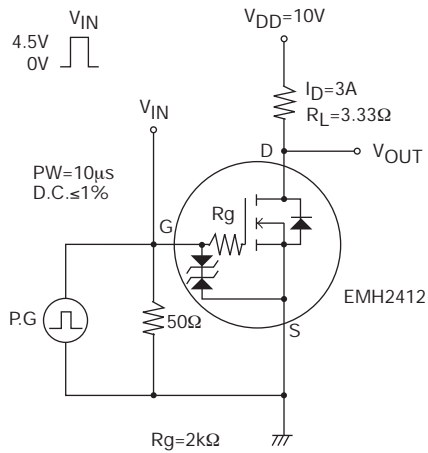


EMH2412

Electrical Characteristics at Ta=25°C

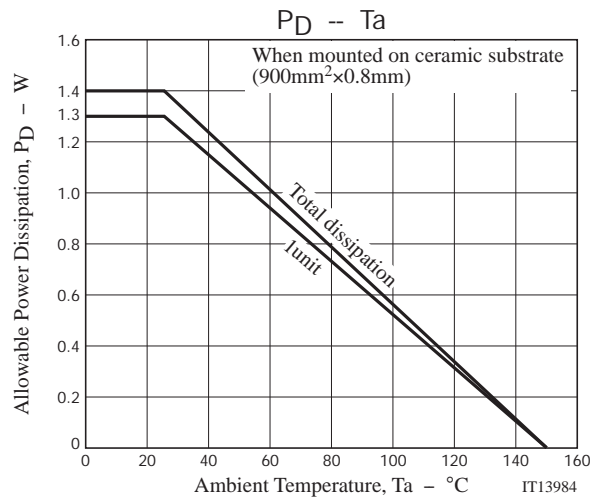
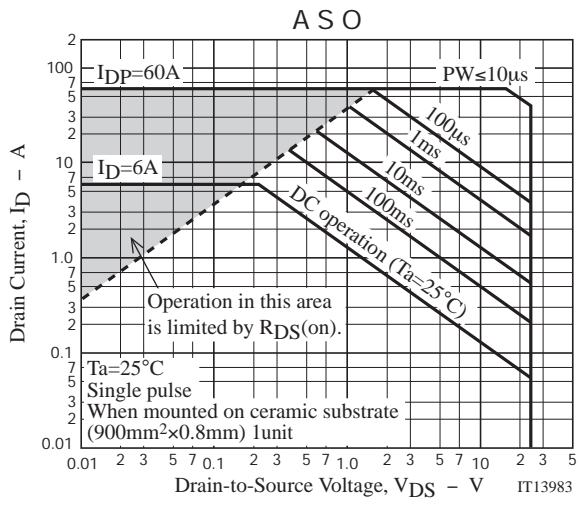
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=1mA, V_{GS}=0V$	24			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS}=20V, V_{GS}=0V$			-1	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 8V, V_{DS}=0V$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS}=10V, I_D=1mA$	0.5		1.3	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS}=10V, I_D=3A$	2.8	4.8		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)1}$	$I_D=3A, V_{GS}=4.5V$	16	21	27	$m\Omega$
	$R_{DS(on)2}$	$I_D=3A, V_{GS}=4V$	17	22	29	$m\Omega$
	$R_{DS(on)3}$	$I_D=3A, V_{GS}=3.1V$	18	25	34	$m\Omega$
	$R_{DS(on)4}$	$I_D=1.5A, V_{GS}=2.5V$	21	30	42	$m\Omega$
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		310		ns
Rise Time	t_r			1020		ns
Turn-OFF Delay Time	$t_{d(off)}$			3000		ns
Fall Time	t_f			2250		ns
Total Gate Charge	Q_g		$V_{DS}=10V, V_{GS}=4.5V, I_D=6A$		6.3	
Gate-to-Source Charge	Q_{gs}			0.83		nC
Gate-to-Drain "Miller" Charge	Q_{gd}			1.9		nC
Diode Forward Voltage	V_{SD}	$I_S=6A, V_{GS}=0V$		0.8	1.2	V

Switching Time Test Circuit



Ordering Information

Device	Package	Shipping	memo
EMH2412-TL-H	EMH8	3,000pcs./reel	Pb Free and Halogen Free



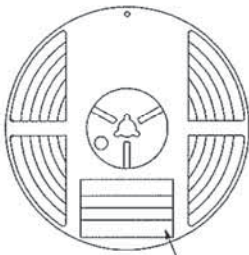
Embossed Taping Specification

EMH2412-TL-H

1. Packing Format

Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)
EMH8	MCP4	3,000	15,000	90,000	5 reels contained Dimensions:mm (external) 183×72×185	6 inner boxes contained Dimensions:mm (external) 440×195×210

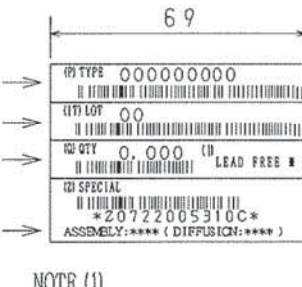
Packing method



Reel label

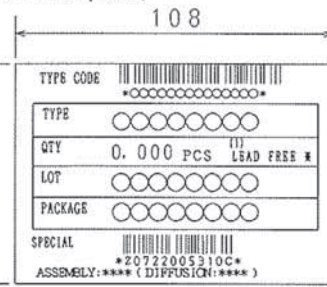
Type No. →
LOT No. →
Quantity →
Origin →

Reel label, Inner box label (unit:mm)



Outer box label

It is a label at the time of factory shipments. The form of a label may change in physical distribution process.



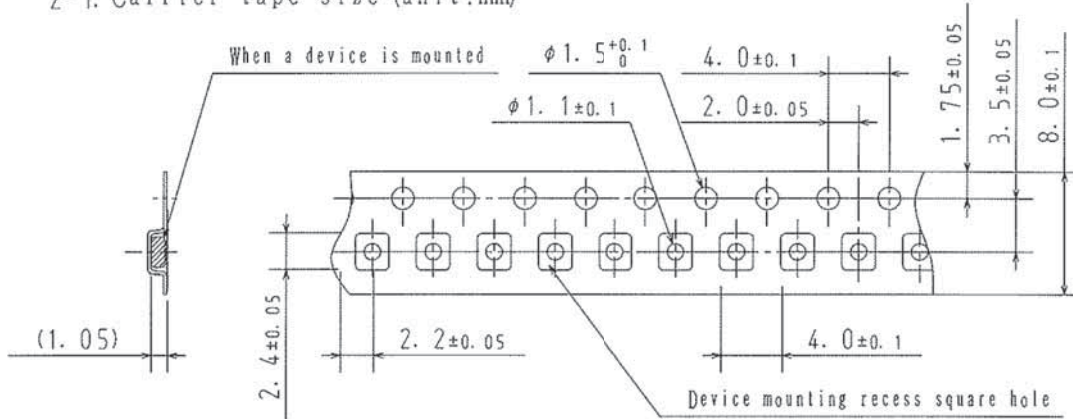
NOTE (1)

The LEAD FREE * description shows that the surface treatment of the terminal is lead free.

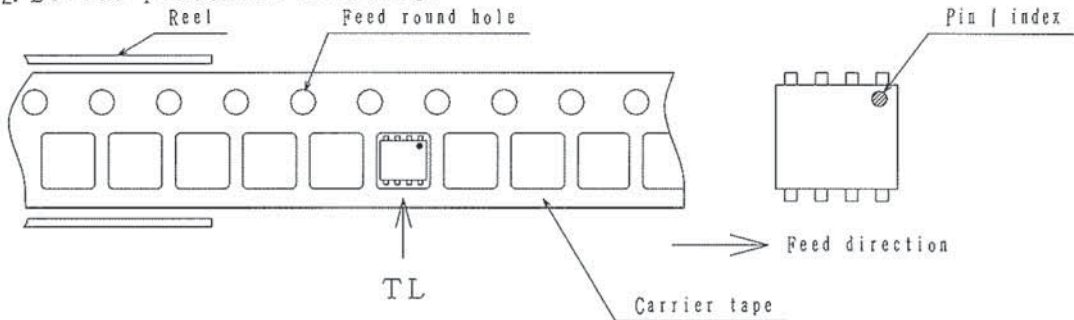
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)



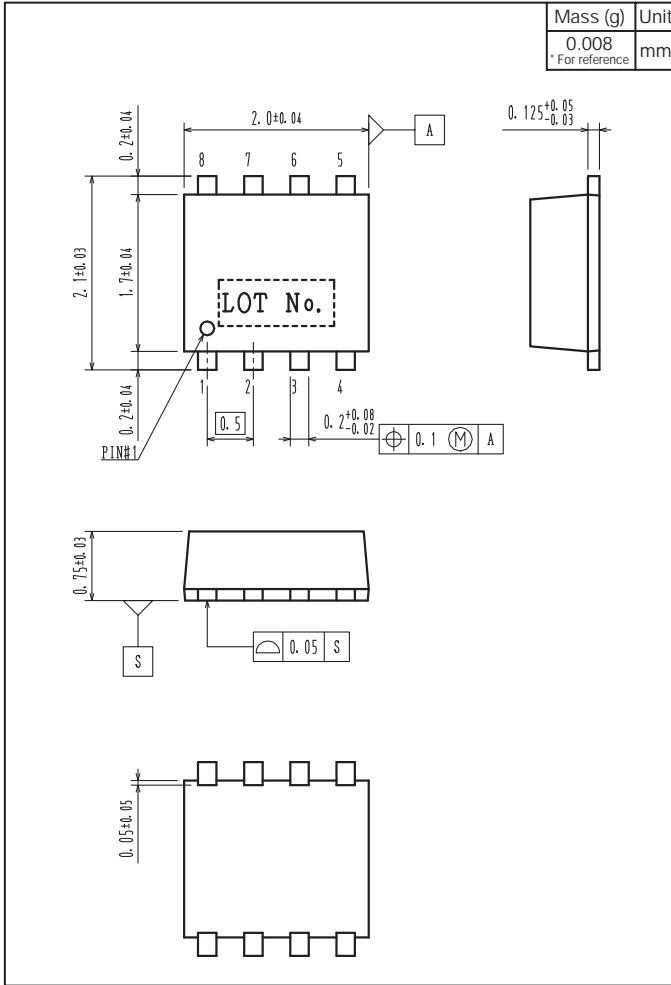
2-2. Device placement direction



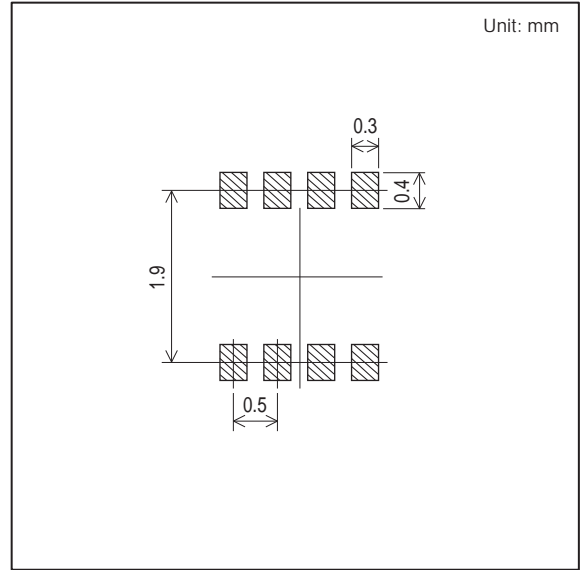
Those with pin | index on the feed hole side.....TL

EMH2412

Outline Drawing EMH2412-TL-H



Land Pattern Example



Note on usage : Since the EMH2412 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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